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## **RENESAS TECHNICAL UPDATE**

TOYOSU FORESIA, 3-2-24, Toyosu, Koto-ku, Tokyo 135-0061, Japan Renesas Electronics Corporation

| Product<br>Category   | MPU/MCU  | Document<br>No.         | TN-RA*-A0140A/E        | Rev.  | 1.00 |  |
|-----------------------|--|-------------------------|------------------------|---|------|--|
| Title                 | Capacitive Sensing Unit (CTSU2) Capacitand reduction characteristics due to power supply noise | Information<br>Category | Technical Notification |   |      |  |
| Applicable<br>Product | RA2L1 Group<br>RA2E1 Group   | Lot No.                 | Reference<br>Document  | RA2L1 User's Manual: Hardware<br>R01UH0853EJ0150 Rev.1.50<br>(Aug. 2024)<br>RA2E1 User's Manual: Hardware<br>R01UH0852EJ0150 Rev.1.50<br>(Jun.2024) |      |  |

## 1. <u>Information regarding the capacitance reduction characteristics due to power supply ripple noise</u>

When ripple noise is superimposed on the VCC power supply, if the ripple noise is superimposed in the frequency band where the control current decreases, the measured value of the capacitance connected to the TSn terminal decreases. This characteristic is presented as a reference value, so please take note of it when designing an external regulator that supplies power to the VCC power supply.

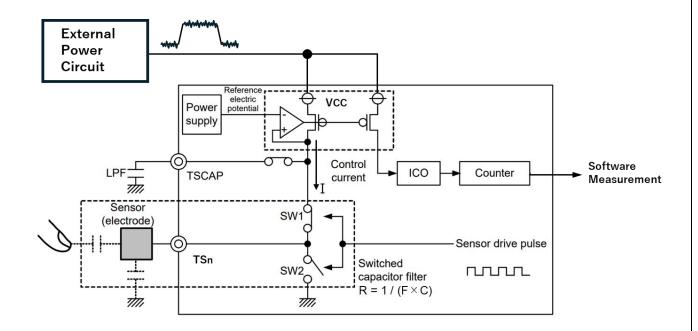


Figure 1 Measurement circuit

For the calculation method of the measured capacitance value of the CTSU2 when ripple noise is superimposed, please refer to " 3.4 Touch Parameter Adjustment (2) RL78/G22 Capacitance / Measurement Value Conversion Formula" and "3.4.2 Example of Countermeasure against False Touch Judgement" in the Application Note Capacitive Touch Ripple Countermeasures Guide (R30AN0453).

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## 2. Characteristic data

Table 1 Capacitive Sensing Unit (CTSU2) Measured capacitance reduction characteristics due to VCC power supply ripple noise (reference value)

Conditions:  $2.4V \le VCC \le 5.5V$ , Vss = 0V, TA = -40 to +105°C, Cp = 20pF

| Item                  |   | Symbol     | Min | Тур | Max  | Unit | Test Conditions<br>(Ripple Noise<br>Amplitude) |  |
|-----------------------|---|------------|-----|-----|------|------|--|--|
|                       | Ripple noise frequency < 20 kHz         | $C_{down}$ | _   | _   | 0.02 | pF   | 100 mVpp                                       |  |
| Measured              | 20 kHz ≤ Ripple noise frequency ≤ 2 MHz |            | _   | _   | 0.06 |      | 40 mVpp  |  |
| capacitance reduction |   |            | _   | _   | 0.10 |      | 60 mVpp  |  |
| characteristics Note  |   |            | _   | _   | 0.33 |      | 100 mVpp                                       |  |
|                       | 2 MHz < Ripple noise frequency          |            | _   | _   | 0.01 |      | 100 mVpp                                       |  |

**Note**. This is the value under the following conditions.

- This is the value when using the Self-capacitance method (CTSUCRAL.MD1 = 0) .
- This is the value when the measured current range is 40uA (CTSUCRAL.ATUNE1 = 1, CTSUCRAH.ATUNE2 = 0). For an overview of measured current range, refer to "2.2 Self-capacitance Method" and "2.2.2 Measurement Range" in the Application Note Capacitive Sensor MCU Capacitive Touch Introduction Guide (R30AN0424)
- The target value for offset adjustment is 37.5%. For an overview of offset adjustment, refer to "2. Capacitance Detection" and "7.1 Automatic Tuning Using QE for Capacitive Touch" in the Application Note Capacitive Sensor MCU Capacitive Touch Introduction Guide (R30AN0424).

Remark. Cp: parasitic capacitance

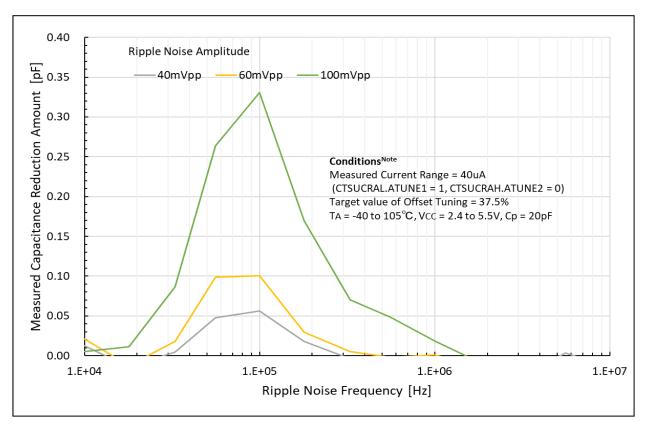


Figure 2 Measured Capacitance Reduction Amount

**Note**. Refer to the application note for Capacitive Sensor MCU, "Capacitive Touch QE for Capacitive Touch Advanced Mode Parameter Guide (R30AN0428)".